TOSHIBA HIGH EFFICIENCY RECTIFIER (HED) SILICON EPITAXIAL JUNCTION TYPE

U1DL49

SWITCHING TYPE POWER SUPPLY APPLICATIONS

• Repetitive Peak Reverse Voltage : V_{RRM}=200V

• Average Forward Current : I_{F (AV)}=1.0A

• Very Fast Reverse Recovery Time : t_{rr}=60ns (Max.)

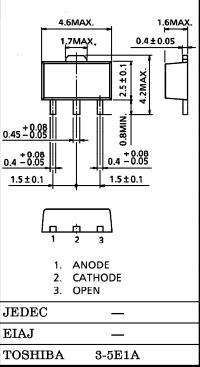
• Low Forward Voltage : V_{FM}=0.98V (Max.)

• Available to Reduce Switching Losses and Output Noise.

MAXIMUM RATINGS

CHARACTERISTIC	SYMBOL	RATING	UNIT	
Repetitive Peak Reverse Voltage	v_{RRM}	200	V	
Average Forward Current	I _{F (AV)}	1.0	Α	
Peak One Cycle Surge Forward	Ta	15 (50Hz)	A	
Current (Non-Repetitive)	I _{FSM}	16.5 (60Hz)		
Junction Temperature	T_{j}	-40~150	°C	
Storage Temperature Range	$\mathbf{T_{stg}}$	-40~150	°C	

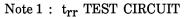
Unit in mm

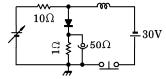


Weight: 0.05g

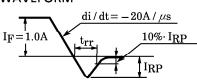
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Peak Forward Voltage	$v_{ m FM}$	$I_{\text{FM}} = 1.0 \text{A}$	_	_	0.98	V
Repetitive Peak Reverse Current	$I_{ m RRM}$	$V_{ m RRM} = 200 V$	_		10	μ A
Reverse Recovery Time (Note 1)	t _{rr}	$I_F = 1A$, di/dt = $-20A/\mu s$	_		60	ns
Forward Recovery Time (Note 2)	t_{fr}	$I_{ m F}$ = 1.0A	_	_	100	ns
Thermal Resistance	R _{th (j-a)}	Junction to Ambient	_		125	°C/W

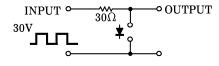




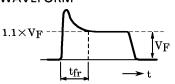
WAVEFORM



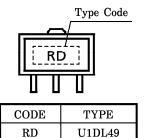
Note 2: tfr TEST CIRCUIT



WAVEFORM

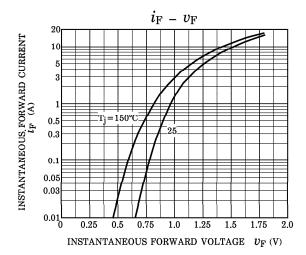


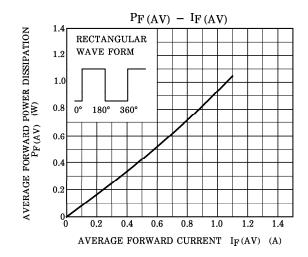
MARKING

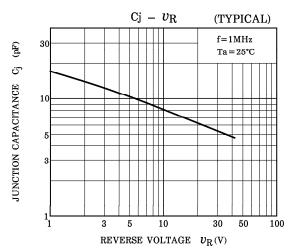


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